



Cite this: *J. Anal. At. Spectrom.*, 2018, 33, 1269

A comparative study of sheathing devices to increase robustness in inductively coupled plasma optical emission spectrometry *via* a nitrogen flow†

Guilherme Luiz Scheffler,^a Dirce Pozebon^a and Diane Beauchemin^b

Five different glass sheathing devices were used to introduce 20 mL min⁻¹ N₂ sheathing gas around the effluent from the spray chamber to see the effect of their dimensions on plasma robustness as measured using the Mg II 280.270 nm/Mg I 285.213 nm emission signal ratio in inductively coupled plasma (ICP) optical emission spectrometry (OES). A clear relationship between device dimensions and the plasma robustness profile along the ICP central channel was observed. With an aerosol inlet having an inner diameter of 1.0 cm in the sheathing device, mixing of N₂ with the aerosol was minimised and the resulting sheath increased robustness, the higher thermal conductivity of N₂ *versus* Ar likely improving energy transfer between the bulk plasma and the central channel. The configuration of the outlet is also important, as any bottleneck favours mixing of N₂ with the aerosol, which in turn cools the plasma, thereby shifting the region of maximum robustness to higher above the load coil. Regardless of device dimensions, plasma robustness was always better with N₂ sheathing gas. An increased ion-to-atom emission signal ratio also resulted for other elements than Mg. The presence of N₂ also seems to affect excitation mechanisms, such as charge transfer between NO⁺ and Cd or Ni, which appears to take place at higher observation height, after N₂ has had enough time to diffuse into the central channel.

Received 26th April 2018
Accepted 22nd May 2018

DOI: 10.1039/c8ja00118a

rsc.li/jaas

Introduction

The energy coupling efficiency between the bulk plasma and its central channel, *i.e.* plasma robustness, is a key parameter in inductively coupled plasma (ICP) spectrometry to ensure adequate sample desolvation, vaporisation, atomisation and ionisation in ICP mass spectrometry (MS), as well as excitation of atoms and ions in ICP optical emission spectrometry (OES).^{1–5} Even though it is well accepted that high applied radiofrequency (RF) power, low nebuliser gas flow rate and use of a wider bore injector lead to robust conditions, common negative side effects of such conditions include increased flicker noise, loss of sensitivity or excessive analyte diffusion in the central channel of the ICP.^{6–9}

Plasma robustness can also be improved by adding a foreign molecular gas to the Ar ICP flow,^{10–13} or as a sheathing gas around the aerosol carrier gas flow,¹⁴ to increase energy transfer through a modification of the fundamental properties of the ICP. For example, adding a small flow of N₂ to the nebuliser gas flow using a tee improved plasma robustness, mitigated matrix

effects and increased ICP excitation temperature.^{15–17} The effect of the foreign gas on robustness depends on the way in which it is added to the plasma, the concurrent water load and the absolute Ar gas flow rates, in addition to the physico-chemical properties of the gas itself. Introducing it as a sheathing gas usually leads to a gas layer between the plasma ring and the central channel.^{3,14}

A sheathing device was first used by Murillo and Mermet³ to add H₂ to the ICP, thereby enhancing the local thermal conductivity and thus increasing the excitation temperature with almost no increase in continuum background, which ultimately improved detection limits. Beauchemin and Craig¹⁷ inserted a sheathing device between the spray chamber and the torch to introduce a low N₂ flow and produce a mixed-gas Ar–N₂ ICP for ICPMS. Although it reduced sensitivity, the sheathing N₂ flow improved stability, reduced mass bias and lowered detection limits in some cases when compared to those obtained with an Ar ICP. A sheathing device may also be useful for O₂ introduction in the ICP to prevent soot deposition when organic solutions are being analysed.¹⁸

Since the early work of Lichte¹⁹ who designed a torch with four gas inlets, including one for an Ar sheathing flow to facilitate the analysis of sample solutions containing a high concentration of salt, the benefits of using a sheathing flow have been recognised. However, no study has been reported on the effect of the design and dimensions of the sheathing device or on sheathing gas flow effects. The emission/ion profiles

^aUniversidade Federal do Rio Grande do Sul, Instituto de Química, Porto Alegre, RS, 91501-970, Brazil. E-mail: guilherme.scheffler@ufrgs.br; dircepoz@iq.ufrgs.br

^bQueen's University, Department of Chemistry, Kingston, ON, K7L 3N6, Canada. E-mail: diane.beauchemin@queensu.ca

† Electronic supplementary information (ESI) available: Tables S1 and S2. See DOI: 10.1039/c8ja00118a

around the central channel of the ICP would provide information about the effect of the device on robustness, foreign gas diffusion or extent of mixing with the plasma Ar flow. Such data would be useful to enable an improvement of available sheathing devices. Therefore, in the current study, the ion-to-atom emission signal ratio of several elements were collected to study the diffusion of the sheathing gas into the central channel.

Experimental

Instrumentation

Measurements were carried out using a lateral-view ARCOS ICPOES instrument (SPECTRO Analytical Instruments, Kleve, Germany) equipped with a Burgener T2100 parallel path nebuliser (Burgener Research, Mississauga, ON, Canada) fitted to a baffled cyclonic spray chamber (SCP Science, Baie d'Urfé, QC, Canada). The ICPOES operating parameters are summarised in Table 1. Five different sheathing devices, shown in Fig. 1, and whose dimensions are summarised in Table 2, were compared for N₂ addition. Commercially available device 1 was compared to home-made devices 2–5. Each device was inserted between the spray chamber and the ICP torch. Emission profiles were collected by automated torch movement (controlled by software). Addition of N₂ to the plasma (outer) gas flow was done through a Y connector. Two mass flow controllers (model

1259C-01000SV, MKS Instruments Inc., Andover, MA, USA) allowed precise N₂ addition. The N₂ flow rates investigated were based on previous works,^{14–16} where the minimum flow rate increasing robustness to a constant value while being tolerable in the central ICP channel was selected.

Chemicals, standards and reference materials

Doubly deionised water (DDW) was obtained from an Arim Pro UV/DI System (Sartorius Stedim Biotech, Goettingen, Germany) and used to prepare solutions and samples. A stock multi-elemental solution (100 mg L⁻¹) was prepared in 5% v/v HNO₃ by dilution of 10 000 mg L⁻¹ mono-elemental standard solutions (SCP Science, Baie d'Urfé, QC, Canada) of Al, As, Cd, Co, Cr, Cu, Fe, K, La, Li, Mg, Mn, Mo, Ni, P, Pb, S, Sb, Sc, Si, Se, Sr, Ti, V, Y, Zn and Zr. Calibration solutions ranging from 0 to 20 mg L⁻¹ were prepared in 5% v/v HNO₃, by serial dilution of the stock solution. A sub-boiling distillation system (DST-1000, Savillex, Minnetonka, MN, USA) was used to purify HNO₃ and HCl (ACS grade, Fisher Scientific, Ottawa, ON, Canada) reagents. Two certified reference materials (SS1 and SS2) contaminated soils from SCP Science were analysed to demonstrate the higher accuracy and robustness with N₂. In each case, 2 mL of aqua regia (prepared 1 h before use) were added to 0.1 g of soil in a glass beaker and heated to 90 °C on a hotplate for 4 h. After cooling, the solutions were diluted to 15 mL with DDW in volumetric flasks.

Results and discussion

Preliminary optimisations of Ar–N₂ ICP

With 0.4 L min⁻¹ of N₂ in the plasma gas and 20 mL min⁻¹ of N₂ sheathing gas around the aerosol gas flow, the Ar plasma gas flow rate was changed from 11 to 15 L min⁻¹ while monitoring the intensities of emission lines having a wide range of excitation energies. Plasma robustness, as assessed using the Mg II 280.270 nm/Mg I 285.213 nm intensity ratio, was 10, 9.95, 9.58, 9.26 and 8.86 at 11, 12, 13, 14 and 15 L min⁻¹ Ar plasma gas flow rate, respectively. As robustness decreased with an increase in Ar plasma gas flow rate, so did analyte emission intensity (see

Table 1 Instrumental operating conditions for ICPOES

| Parameter | Value |
|--|--------------------------|
| Radio frequency power | 1.4 kW |
| Ar plasma gas flow rate | 12.0 L min ⁻¹ |
| N ₂ flow rate in the plasma (outer) gas | 0.4 L min ⁻¹ |
| Ar auxiliary gas flow rate | 1.0 L min ⁻¹ |
| Ar aerosol carrier gas flow rate | 0.70 L min ⁻¹ |
| N ₂ sheathing gas flow rate | 20 mL min ⁻¹ |
| Sample uptake rate | 1.0 mL min ⁻¹ |
| Observation height above the load coil (ALC) | 10–20 mm |
| Integration time | 28 s |

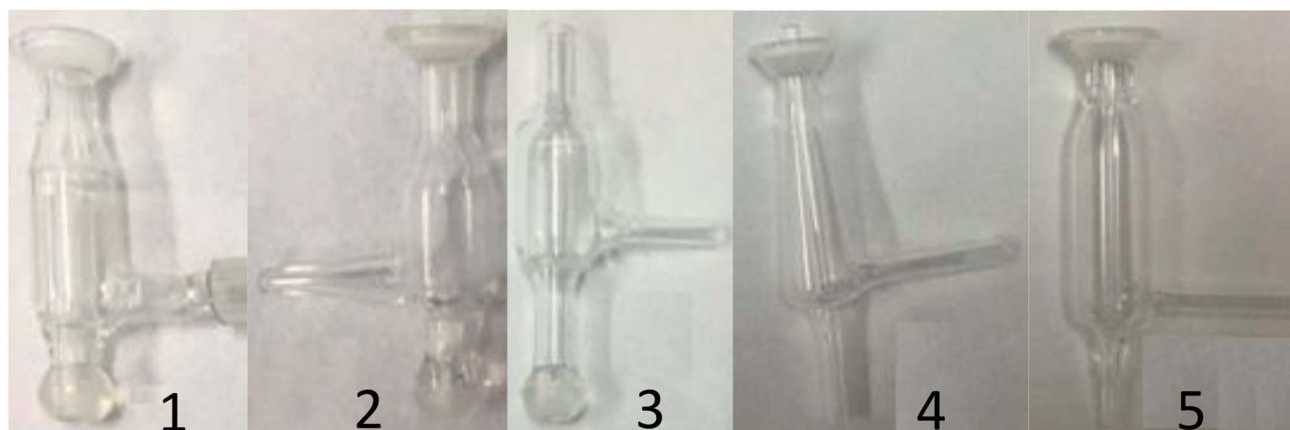


Fig. 1 Devices used to add 20 mL min⁻¹ N₂ sheathing gas.

Table 2 Dimensions of the devices inserted between the spray chamber and the ICP torch for N₂ addition as sheathing gas

| Device | 1 | 2 | 3 | 4 | 5 |
|-----------------------------------|--------------------------------|--------------------------------|--------------------------------|--------------------------------|--------------------------------|
| Length | 8.0 cm | 6.5 cm | 7.5 cm | 7.5 cm | 7.5 cm |
| Internal diameter of aerosol tube | 1.0 cm | 1.0 cm | 5 mm | 3 mm | 2 mm |
| Central tube length | 5.0 cm | 4.0 cm | 5.0 cm | 7.8 cm | 7.5 cm |
| Device diameter | 1.5 cm (base) to 1.0 cm (neck) | 1.5 cm (base) to 1.0 cm (neck) | 1.5 cm (base) to 0.5 cm (neck) | 1.5 cm (base) to 1.0 cm (neck) | 1.5 cm (base) to 1.0 cm (neck) |

Table S1†), irrespectively of excitation energy in most cases. This is a result of the N₂ concentration decreasing in the plasma as the Ar flow rate increases, in turn decreasing the power density in the ICP. Because the ICP may extinguish (and melt the torch) when the plasma gas flow rate is as low as 11 L min⁻¹, the Ar plasma gas flow rate was kept at 12 L min⁻¹ for the remainder of this work. The same flow rate was previously used on the same instrument for a mixed-gas plasma involving N₂ addition to the plasma gas and H₂ introduction as a sheath gas.¹²

Analyte emission intensities were also monitored as the auxiliary gas flow rate was increased from 0.6 to 3.0 L min⁻¹. Again, intensities and plasma robustness decreased with an increase in auxiliary gas flow rate (see Table S2†). This is due to the concurrent displacement of the analytical zone. However, when the auxiliary gas flow rate was 0.6 L min⁻¹, the ICP was unstable. To avoid plasma extinction, the auxiliary gas flow rate was fixed at 1.0 L min⁻¹. This is again consistent with that found by multivariate optimisation for the above mentioned Ar-N₂-H₂ plasma.¹²

Fig. 2 shows that, in most cases, the highest signal intensities were obtained when the nebuliser gas flow rate was 0.70 L min⁻¹. Plasma robustness (not shown) decreased as the nebuliser gas flow rate increased above this value, down to that commonly observed with an Ar ICP. Given that a similar optimum nebuliser gas flow rate was also found for devices 2 and 3, the nebuliser gas flow rate was fixed at 0.70 L min⁻¹. In Fig. 2, two atomic emission lines with low excitation energy (K I and Li I) behave differently. Given that the Li I intensity is not strongly affected by the presence of N₂ (see Table S1†), the rise in Li I intensity with an increase in nebuliser gas flow rate likely reflects the shorter residence time in the plasma, which decreases the Li II population within the observation region. In the case of K I, the signal decrease is a result of an increase in background caused by the addition of N₂.

Sheathing devices evaluation

Sheathing devices allow part of the additional gas not to mix with the nebulised aerosol flow, in contrast to adding the gas through a T or Y connection. Because the geometry and size of the sheathing device may affect the extent of mixing, different modifications were made, where the length, diameter of the aerosol inlet tube and design of the outlet were varied, as shown in Fig. 1 and detailed in Table 2. The plasma robustness criterion was used to compare the various devices shown in Fig. 1, with and without the sole addition of N₂ as sheathing gas to the

ICP so as to clearly see the effect of the sheathing gas. A single set of operating conditions (listed in Table 1, except that no N₂ was added to the plasma gas) was used for the comparison, even if it was not optimal for all devices, in order to rule out the effect of other operating parameters, such as a change in sample

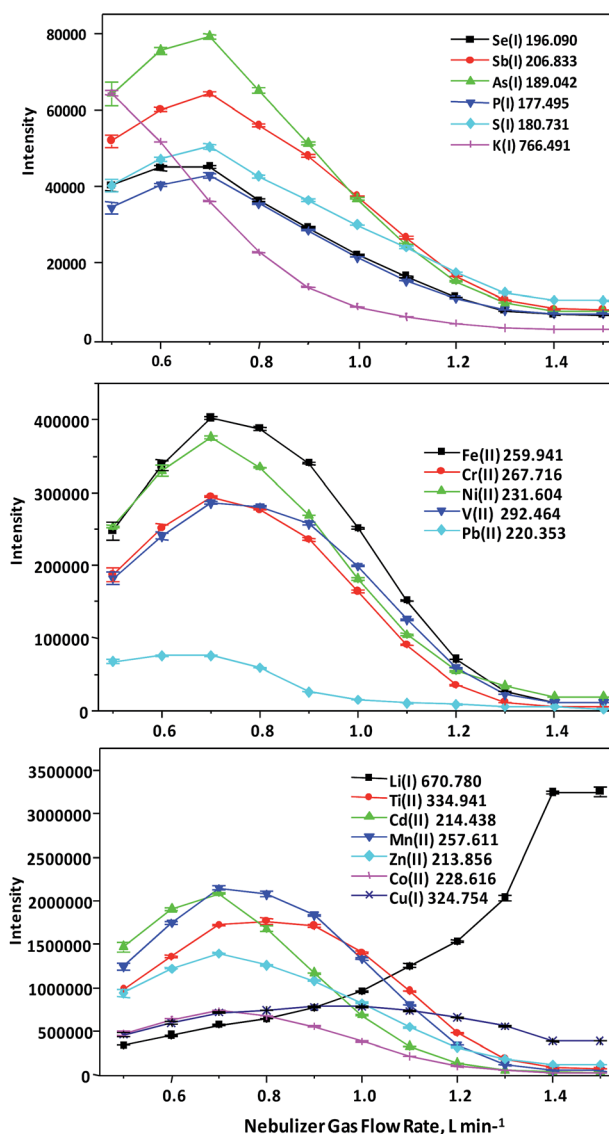


Fig. 2 Effect of the nebuliser gas flow rate on background-corrected analyte intensities measured at 10 mm ALC for a 5 mg L⁻¹ multi-element solution with 400 mL min⁻¹ N₂ in the plasma gas and 20 mL min⁻¹ N₂ sheathing gas through device 1.

introduction efficiency associated with a change in aerosol carrier gas flow rate. To study diffusion of the N₂ sheath gas, the robustness was monitored at different observation heights. The results are summarised in Table 3 where, regardless of the device used and observation height, the robustness of the plasma was always better with N₂ sheathing gas.

Without N₂ sheathing gas, the maximum robustness is observed at 10 mm ALC, irrespectively of the sheathing device, except with device 2, where the maximum is at 12 mm ALC although robustness does not change much from 10 to 14 mm ALC with device 2 (as well as device 3). Given the similarities between devices 1 and 2, including in axial velocity (which should be constant, as the same aerosol carrier gas flow rate was used in all cases), this comparison reveals that even small differences in dimensions can have a very significant impact on the Ar ICP. In any case, the internal diameter of the aerosol tube in the sheathing device clearly has no effect on the observation position of maximum robustness when no sheathing gas is used.

The impact of differences in sheathing device dimensions is even more evident upon the sole addition of N₂ as a sheathing gas to the plasma. The best height for robustness is similar to that without sheathing gas with devices 1 and 2, despite the higher axial velocity that would be expected from the addition of 20 mL min⁻¹ N₂ sheathing gas if thorough mixing of N₂ with the aerosol occurred. In contrast, increasing the observation height by 3–6 mm is required with N₂ sheathing gas for devices 3–5, which have a narrower internal tube. As the total axial velocity should be the same for all devices, the aerosol carrier gas and the sheathing gas flow rates being constant, the shift in position of maximum robustness due to an increase in axial velocity from N₂ addition should be independent of the device. Clearly then, the differences in position of maximum robustness between the devices can only be ascribed to the N₂ sheathing gas and differences in fluid dynamics arising from the different sheathing device designs.

The gradual decrease from 1.5 to 1.0 cm at the outlet of device 1 ensures that N₂ mostly remains around the central channel. Hence, the axial velocity of the aerosol and thus the observation height for maximum robustness remain as if no sheathing gas was present. Only an increase in robustness is observed, from the energy transfer that is likely promoted by the higher thermal conductivity of N₂ versus Ar. In contrast, the constant 1.0 cm length over 1.6 cm at the outlet of device 2 leads to more mixing of N₂ with Ar in the central channel, thereby increasing the apparent axial velocity of the aerosol and cooling the plasma. This results in a shift in the position of maximum robustness to slightly higher in the ICP.

The greatest shift in the position of maximum robustness is achieved with device 3 because of the higher axial velocity of the aerosol caused by the smaller diameter of the outlet, along with its longer neck, which favours mixing of N₂ with the aerosol. Judging from the shift of maximum robustness to higher ALC, some mixing of N₂ with the aerosol also seems to occur with devices 4 and 5, despite the internal tube extending outside the sheathing device. If no mixing with N₂ occurred and only a change in axial velocity was at play, then the shift would be greater with device 5 than device 4, as its aerosol tube is smaller than that of device 5. With device 4, a similar robustness is nonetheless achieved at 14 mm ALC as with device 1 at 10 mm ALC. Given that device 1 provides the highest robustness with and without N₂ sheathing gas, it was selected for subsequent studies.

Other signal ratios

Fig. 3 shows the ion-to-atom intensity ratio obtained for Cd, Cu and Ni, as well as the Ba II/Mn II ratio. The latter was monitored because it increases with the overpopulation of metastable Ar (Ar^m) species.^{20,21} The Cd II/Cd I profiles in Fig. 3 suggest different excitation mechanisms in the Ar ICP and Ar–N₂ ICP. In particular, the increase of the ratio at greater distances ALC in the Ar–N₂ ICP may be caused by charge transfer with NO⁺

Table 3 Plasma robustness (Mg II 280 nm/Mg I 285 nm emission intensity ratio) at different observation heights ALC without (the sheathing gas inlet was sealed) and with 20 mL min⁻¹ N₂ sheathing gas using the devices in Fig. 1 (without addition of N₂ to the plasma gas flow), where the maximum robustness is highlighted in each case

| Observation height ALC, mm | Sheathing device | | | | | | | | | |
|----------------------------|---------------------|------------------------|---------------------|------------------------|---------------------|------------------------|---------------------|------------------------|---------------------|------------------------|
| | 1 | | 2 | | 3 | | 4 | | 5 | |
| | With N ₂ | Without N ₂ | With N ₂ | Without N ₂ | With N ₂ | Without N ₂ | With N ₂ | Without N ₂ | With N ₂ | Without N ₂ |
| 10 | 8.08 | 5.12 | 7.12 | 3.68 | 5.33 | 3.47 | 7.61 | 4.20 | 6.67 | 3.99 |
| 11 | 7.86 | 4.64 | 7.14 | 3.73 | 5.33 | 3.46 | 7.57 | 4.14 | 7.07 | 3.97 |
| 12 | 6.98 | 4.46 | 7.50 | 3.78 | 5.74 | 3.47 | 7.64 | 4.07 | 7.33 | 3.92 |
| 13 | 7.34 | 4.27 | 7.53 | 3.73 | 5.96 | 3.44 | 7.91 | 4.00 | 7.45 | 3.85 |
| 14 | 6.66 | 4.07 | 7.47 | 3.73 | 6.11 | 3.42 | 8.07 | 3.87 | 7.41 | 3.79 |
| 15 | 6.55 | 3.71 | 7.33 | 3.61 | 6.26 | 3.31 | 7.68 | 3.82 | 7.40 | 3.74 |
| 16 | 6.52 | 3.36 | 7.14 | 3.50 | 6.31 | 3.23 | 7.08 | 3.69 | 7.16 | 3.65 |
| 17 | 6.77 | 3.32 | 6.84 | 3.38 | 6.20 | 3.15 | 6.88 | 3.55 | 6.96 | 3.55 |
| 18 | 6.22 | 3.59 | 6.61 | 3.29 | 6.06 | 3.06 | 6.61 | 3.46 | 6.64 | 3.42 |
| 19 | 5.40 | 3.19 | 6.26 | 3.19 | 5.93 | 2.97 | 6.26 | 3.33 | 6.29 | 3.31 |
| 20 | 4.96 | 2.91 | 5.89 | 3.11 | 5.64 | 2.90 | 6.02 | 3.26 | 6.04 | 3.21 |

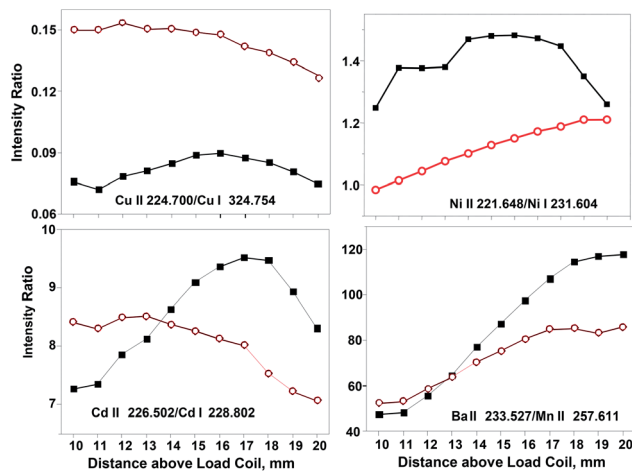


Fig. 3 Selected signal ratios at different observation heights ALC (without N₂ in the plasma gas flow) without (red open circles) and with (black full squares) 20 mL min⁻¹ N₂ sheathing gas added using device 1.

(ionisation energy = 9.26 eV), which promotes the ionisation of Cd (ionisation energy = 8.99 eV). The same process likely explains the difference between the Ni II/Ni I ratio profiles with and without N₂. The Cu ratio anomaly, where the ratio in the Ar-N₂ ICP is systematically lower than that in an Ar ICP, corroborate previous results obtained when a low flow of N₂ was added to the ICP.¹⁶ The addition of N₂ may induce an overpopulation of Ar^m, which decreases the Cu ion population, thereby increasing that of Cu atoms. This phenomenon is lesser in the Ar ICP because the amount of N₂ present (from atmospheric air entrainment and HNO₃ present in the solution) is much lower. With respect to the Ba II/Mn II ratio, the increase of Ba II may result from the energy closeness of Ba II (11.21 eV) to that of Ar^m (11.55 eV). The fact that similar excitation mechanisms were observed when the same quantity of N₂ was introduced through a T device¹⁶ seems to indicate that they are independent of the device type, *i.e.* sheathing device or T, and mostly depend on the foreign gas entering the ICP.

Conclusions

The robustness of the ICP was improved with 20 mL min⁻¹ N₂ sheathing gas irrespectively of the sheathing device dimensions. However, those dimensions have a great impact on plasma robustness, as they may affect the axial velocity of the aerosol and the extent of mixing with N₂ as well as any energy transfer from the bulk plasma to the central channel that may be promoted by the high thermal conductivity of N₂, drastically affecting the analytical characteristics of the resulting ICP. The higher robustness is also reflected by emission signal ratios of other elements. Future studies will include modifications of device 1 to improve the performance of electrothermal vapourisation (ETV) coupled to ICPOES. Aerosol pre-evaporation, like was previously done to simultaneously introduce water vapour with the ETV effluent to increase plasma robustness,²² will also

be tested to eliminate condensation in the device, which constitutes its main problem.

Conflicts of interest

There are no conflicts to declare.

Acknowledgements

The authors gratefully acknowledge the financial support of the National Science and Engineering Research Council of Canada (grant number 39487-2013) and Anglo American Pty for the donation of the ARCOS ICPOES instrument. GLS received a CNPq scholarship in Canada (201398/2015-0) while DP is grateful for a CNPq research fellowship in Brazil.

References

- 1 J.-M. Mermet, *Spectrochim. Acta, Part B*, 1989, **44**, 1109–1116.
- 2 J.-M. Mermet, *Anal. Chim. Acta*, 1991, **250**, 85–94.
- 3 M. Murillo and J.-M. Mermet, *Spectrochim. Acta, Part B*, 1989, **44**, 359–366.
- 4 D. Beauchemin, *Mass Spectrom. Rev.*, 2010, **29**, 560–592.
- 5 M. Murillo and J.-M. Mermet, *Spectrochim. Acta, Part B*, 1987, **42**, 1151–1162.
- 6 J.-M. Mermet, *Anal. Chim. Acta*, 1991, **250**, 85–94.
- 7 X. Romero, E. Poussel and J.-M. Mermet, *Spectrochim. Acta, Part B*, 1997, **52**, 487–493.
- 8 J. W. Tromp, M. Pomares, M. Alvarez-Prieto, A. Cole, H. Ying and E. D. Salin, *Spectrochim. Acta, Part B*, 2003, **58**, 1927–1944.
- 9 H. P. Longerich, B. J. Fryer, D. F. Strong and C. J. Kantipuly, *Spectrochim. Acta, Part B*, 1987, **42**, 75–92.
- 10 Y. Makonnen and D. Beauchemin, *Spectrochim. Acta, Part B*, 2014, **99**, 87–93.
- 11 Y. Makonnen and D. Beauchemin, *Spectrochim. Acta, Part B*, 2015, **103–104**, 57–62.
- 12 Y. Makonnen, W. R. MacFarlane, M. L. Geagea and D. Beauchemin, *J. Anal. At. Spectrom.*, 2017, **32**, 1688–1696.
- 13 S. M. Burchell, MSc thesis, Queen's University, 2000.
- 14 G. L. Scheffler and D. Pozebon, *J. Anal. At. Spectrom.*, 2015, **30**, 468–478.
- 15 G. L. Scheffler and D. Pozebon, *Spectrochim. Acta, Part B*, 2015, **113**, 84–92.
- 16 G. L. Scheffler, C. A. Martins and D. Pozebon, *J. Anal. At. Spectrom.*, 2016, **31**, 1141–1149.
- 17 D. Beauchemin and J. M. Craig, *Spectrochim. Acta, Part B*, 1991, **46**, 603–614.
- 18 D. Hausler, *Spectrochim. Acta, Part B*, 1987, **42**, 63–73.
- 19 F. E. Lichte, A. L. Meier and J. G. Crock, *Anal. Chem.*, 1987, **59**, 1150–1157.
- 20 X. Romero, E. Poussel and J. M. Mermet, *Spectrochim. Acta, Part B*, 1997, **52**, 487–493.
- 21 X. Romero, E. Poussel and J. M. Mermet, *Spectrochim. Acta, Part B*, 1997, **52**, 495–502.
- 22 N. Sadiq, L. Huang, F. Kaveh and D. Beauchemin, *Food Chem.*, 2017, **237**, 1–6.



Journal Name

ARTICLE

Table S1. Influence of the plasma (outer) gas flow rate on emission lines intensities for a solution containing 5 mg L⁻¹ of the elements; 400 mL min⁻¹ N₂ and 20 mL min⁻¹ N₂ were respectively added to the plasma and nebulizer gas flows.

| Wavelengths | Energy*, eV | 11 L min ⁻¹ | 12 L min ⁻¹ | 13 L min ⁻¹ | 14 L min ⁻¹ | 15 L min ⁻¹ | Ratio 11/15 |
|---------------|-------------|------------------------|------------------------|------------------------|------------------------|------------------------|-------------|
| Se I 196.090 | 6.32 | 72000±840 | 63900±600 | 54700±650 | 49200±300 | 44000±400 | 1.63 |
| Sb I 206.833 | 5.98 | 82600±770 | 75300±340 | 66820±580 | 61730±150 | 57000±400 | 1.45 |
| As I 189.042 | 6.56 | 107400±1400 | 96700±830 | 83550±860 | 75330±340 | 67700±500 | 1.58 |
| P I 177.495 | 6.99 | 60100±700 | 53640±560 | 46470±270 | 42000±370 | 38000±300 | 1.58 |
| S I 180.731 | 6.85 | 68400±630 | 62150±640 | 54450±600 | 50000±300 | 45840±250 | 1.49 |
| K I 766.491 | 1.62 | 31700±450 | 26900±500 | 22340±290 | 19350±180 | 17000±190 | 1.86 |
| Li I 670.780 | 1.85 | 774600±4500 | 760400±13900 | 734500±4300 | 726200±680 | 712700±5300 | 1.08 |
| Fe II 259.941 | 13.09 | 628000±3000 | 579660±9500 | 524800±5500 | 488000±5800 | 452900±2300 | 1.38 |
| Cr II 267.716 | 12.95 | 457500±3900 | 422000±4400 | 378300±2500 | 348500±3700 | 319700±2400 | 1.43 |
| Ni II 231.604 | 14.03 | 605600±5000 | 542000±6000 | 472400±3000 | 423600±6100 | 380760±3600 | 1.59 |
| V II 292.464 | 11.37 | 437300±3700 | 408400±5300 | 375600±3200 | 354100±2900 | 331000±1900 | 1.32 |
| Pb II 220.353 | 14.79 | 103300±1600 | 88800±1200 | 73780±940 | 64000±460 | 56100±550 | 1.84 |
| Ti II 334.941 | 10.56 | 2572800±19000 | 2435000±36000 | 2289000±18000 | 2198000±18000 | 2090000±28000 | 1.23 |
| Cd II 214.438 | 14.77 | 3300000±21000 | 2861550±47000 | 2388000±33000 | 2106000±36000 | 1809000±29000 | 1.82 |
| Mn II 257.611 | 12.25 | 3312000±26000 | 3068000±46000 | 2792000±28000 | 26167000±23000 | 2420000±34000 | 1.37 |
| Zn II 213.856 | 15.51 | 1812000±12000 | 1658000±23000 | 1493000±11000 | 1392000±16000 | 1288000±13000 | 1.40 |
| Co II 228.616 | 13.70 | 1190100±10300 | 1077000±11000 | 948600±7200 | 858000±11000 | 777900±7000 | 1.53 |
| Cu I 324.754 | 3.82 | 938400±6600 | 911000±15000 | 869000±5000 | 854400±4500 | 831800±1600 | 1.13 |
| Mg II 280.270 | 12.07 | 8216000±41000 | 7650000±110000 | 6909000±51000 | 64435000±66000 | 5907000±83000 | 1.39 |
| Mg I 285.213 | 4.34 | 808600±6000 | 768700±9300 | 721100±4500 | 695400±4700 | 666100±1200 | 1.21 |

*Obtained from <https://www.nist.gov/pml/atomic-spectra-database>, which lists the excitation energy for atomic lines and the sum of the excitation and ionization energies for ionic lines.

Table S2. Influence of the auxiliary gas flow rate on emission lines intensities for a solution containing 5 mg L⁻¹ of the elements; 400 mL min⁻¹ N₂ and 20 mL min⁻¹ N₂ were respectively added to the plasma and nebulizer gas flows.

| Wavelength, nm | 3.0 L min ⁻¹ | 2.5 L min ⁻¹ | 2.0 L min ⁻¹ | 1.5 L min ⁻¹ | 1.0 L min ⁻¹ | 0.6 L min ⁻¹ | Ratio 1.0/3.0 |
|--------------------|-------------------------|-------------------------|-------------------------|-------------------------|-------------------------|-------------------------|---------------|
| Se I 196.090 | 38000±350 | 42157±800 | 49000±300 | 56700±280 | 62710±500 | 65800±400 | 1.65 |
| Sb I 206.833 | 42500±400 | 48650±800 | 57700±200 | 67000±390 | 74500±400 | 78900±400 | 1.75 |
| As I 189.042 | 53680±670 | 61000±1000 | 72500±600 | 85000±700 | 95000±450 | 99800±800 | 1.76 |
| P I 177.495 | 34260±150 | 37200±700 | 42500±200 | 48500±250 | 53000±200 | 55100±300 | 1.54 |
| S I 180.731 | 40900±470 | 43000±700 | 48600±450 | 55250±300 | 60800±280 | 63800±800 | 1.48 |
| K I 766.491 | 14800±70 | 15700±100 | 17800±160 | 21500±700 | 26100±200 | 28150±800 | 1.76 |
| Li I 670.780 | 931900±960 | 846200±6500 | 825700±2450 | 801600±22100 | 764700±4300 | 750800±6400 | 0.82 |
| Fe II 259.941 | 338000±3000 | 401300±60000 | 483500±2500 | 547600±6900 | 582000±5700 | 600000±4700 | 1.72 |
| Cr II 267.716 | 229200±950 | 279400±3800 | 341400±2600 | 391300±5200 | 419400±5000 | 432500±6700 | 1.82 |
| Ni II 231.604 | 256600±2000 | 320000±5200 | 403200±4300 | 478600±4400 | 537600±7300 | 562300±12000 | 2.09 |
| V II 292.464 | 260800±1200 | 303200±3100 | 356300±2400 | 394000±6000 | 411200±4200 | 419300±6400 | 1.57 |
| Pb II 220.353 | 30960±300 | 41600±1200 | 56400±100 | 73200±1100 | 87300±400 | 96200±1200 | 2.82 |
| Ti II 334.941 | 1723000±37000 | 1939600±24900 | 2267720±11000 | 2427000±35000 | 2455000±26000 | 2487000±33000 | 1.42 |
| Cd II 214.438 | 1088700±8600 | 1365600±21700 | 1883500±13900 | 2389000±26000 | 2794000±100000 | 3038000±25000 | 2.56 |
| Mn II 257.611 | 1784000±39000 | 2107400±26500 | 2606480±16900 | 2920000±21000 | 3064000±52000 | 3150000±33000 | 1.71 |
| Zn II 213.856 | 955700±9400 | 1084600±19200 | 1291800±9900 | 1486300±1600 | 1637830±33000 | 1740000±17000 | 1.71 |
| Co II 228.616 | 535400±4300 | 660400±9600 | 822400±8300 | 964300±10000 | 1073000±13000 | 1117000±19000 | 2.00 |
| Cu I 324.754 | 778100±300 | 804500±7500 | 877450±4000 | 917000±19000 | 915000±8000 | 912000±10000 | 1.17 |
| Mg II 280.270 | 4325000±83000 | 5168000±71000 | 6401450±37750 | 7208000±70000 | 7500000±1200000 | 7680000±99000 | 1.74 |
| Mg I 285.213 | 494700±1000 | 571000±5500 | 669600±4300 | 740300±10000 | 772000±8000 | 783000±10000 | 1.56 |
| Mg II 280/Mg I 285 | 8.74±0.16 | 9.05±0.12 | 9.56±0.05 | 9.73±0.09 | 9.77±0.16 | 9.80±0.12 | - |